Xue-Sen Wang

List of Publications by Year
in descending order

83 papers	1,864 citations	257450 24 h-index	276875 41 g-index
83 all docs	83 docs citations	83 times ranked	1768 citing authors

#	Article	IF	Citations
1	Electron-beam-induced degradation of halide-perovskite-related semiconductor nanomaterials. Chinese Optics Letters, 2021, 19, 030002.	2.9	8
2	Transformation and degradation of metal halide perovskites induced by energetic electrons and their practical implications. Nano Futures, 2021, 5, 032001.	2.2	4
3	Epitaxial growth of black phosphorene enabled on black-phosphorene-like group IV-VI substrates. Physical Review B, 2021, 104, .	3.2	3
4	The charge transfer mechanism of Bi modified TiO 2 nanotube arrays: TiO 2 serving as a â€œcharge-transfer-bridgeâ€• Nano Energy, 2017, 31, 96-104.	16.0	103
5	Multiple unpinned Dirac points in group-Va single-layers with phosphorene structure. Npj Computational Materials, 2016, 2, .	8.7	57
6	Realization of Dirac Cones in Few Bilayer Sb(111) Films by Surface Modification. Nanoscale Research Letters, 2015, 10, 1043.	5.7	9
7	Topological Properties Determined by Atomic Buckling in Self-Assembled Ultrathin Bi(110). Nano Letters, 2015, 15, 80-87.	9.1	191
8	Evolution of Topological Surface States in Antimony Ultra-Thin Films. Scientific Reports, 2013, 3, 2010.	3.3	38
9	Growth of self-assembled Mn, Sb and MnSb nanostructures on highly oriented pyrolytic graphite. Thin Solid Films, 2012, 520, 6909-6915.	1.8	5
10	Size-tunable Au nanoparticles on MoS₂(0001). Nanotechnology, 2012, 23, 375603.	2.6	5
11	Interaction of copper with sulfur on the sulfur-terminated Si(111)-(7Ã—7) surface. Applied Surface Science, 2011, 257, 2038-2041.	6.1	3
12	Observation of a surface alloying-to-dealloying transition during growth of Bi on Ag(111). Physical Review B, 2011, 83, .	3.2	33
13	Growth of well-aligned Bi nanowire on Ag(111). Applied Surface Science, 2009, 256, 460-464.	6.1	26
14	Scanning tunneling microscopy investigation of growth of self-assembled indium and aluminum nanostructures on inert substrates. Thin Solid Films, 2009, 517, 4540-4547.	1.8	2
15	Shape-Controlled Growth of Indium and Aluminum Nanostructures on MoS₂(0001). Journal of Nanoscience and Nanotechnology, 2008, 8, 2707-2712.	0.9	1
16	Molecular anchor Cuâ€“S formed on a thiophene mediated Si(111)-(7Ã—7) surface. Journal of Chemical Physics, 2008, 128, 044706.	3.0	0
17	Nucleation and growth of aluminum on an inert substrate of graphite. Journal of Physics Condensed Matter, 2008, 20, 225002.	1.8	4
18	Scanning tunneling microscopy study of higher-order Si(100)-c(8 Ã— 8) surface reconstruction. Journal of Physics Condensed Matter, 2008, 20, 395003.	1.8	1

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19	Growth of zirconium silicide nanostructures on vicinal and flat Si(111)-7 Ã— 7 surfaces. Journal of Physics Condensed Matter, 2008, 20, 225015.	1.8	4
20	â€œZigzagâ€•C60 chain arrays. Applied Physics Letters, 2008, 92, 023105.	3.3	21
21	Quantitative analysis of Si mass transport during formation ofCuâˆ•Si(111)â^'(5Ã—5)from scanning tunneling microscopy. Physical Review B, 2007, 75, .	3.2	7
22	Morphology, surface structures, and magnetic properties of MnSb thin films and nanocrystallites grown on graphite. Journal of Applied Physics, 2007, 102, 023906.	2.5	5
23	Synthesis and magnetic properties of MnSb nanoparticles on Si-based substrates. Applied Physics Letters, 2007, 90, 202503.	3.3	17
24	C₆₀ Molecular Chains on Î±â€Sexithiophene Nanostripes. Small, 2007, 3, 2015-2018.	10.0	63
25	Self-assembled Ge, Sb and Al nanostructures on graphite: comparative STM studies. Nanotechnology, 2007, 18, 145501.	2.6	11
26	Different-dimensional structures of antimony formed selectively on graphite. Applied Physics A: Materials Science and Processing, 2007, 88, 299-307.	2.3	7
27	Nanoparticles, Nanorods, and Other Nanostructures Assembled on Inert Substrates. , 2007, , 118-153.		0
28	Formation of copper clusters on a thiophene mediated Si(111)-(7Ã—7) surface via molecular anchors. Applied Physics Letters, 2006, 88, 123106.	3.3	4
29	Surface morphology of crystalline antimony islands on graphite at room temperature. Journal of Physics Condensed Matter, 2006, 18, 3425-3434.	1.8	7
30	Electronic structure of Co-induced magic clusters grown onSi(111)â^'(7Ã—7): Scanning tunneling microscopy and spectroscopy and real-space multiple-scattering calculations. Physical Review B, 2006, 73, .	3.2	23
31	Self-assembly of antimony nanowires on graphite. Applied Physics Letters, 2006, 88, 233105.	3.3	25
32	Terrace width dependence of cobalt silicide nucleation on Si(111)-(7Ã—7). Applied Physics Letters, 2006, 88, 023121.	3.3	20
33	DIFFERENT GROWTH BEHAVIOR OF Ge, Al AND Sb ON GRAPHITE. Surface Review and Letters, 2006, 13, 287-296.	1.1	4
34	IN SITU STM INVESTIGATION OF Ge NANOSTRUCTURES WITH AND WITHOUT Sb ON GRAPHITE. Surface Review and Letters, 2006, 13, 241-249.	1.1	3
35	Reactive Co magic cluster formation onSi(111)â^'(7Ã—7). Physical Review B, 2005, 72, .	3.2	45
36	Selective Attachment of 1,4-Benzenedimethanethiol on the Copper Mediated Si(111)â^'(7 Ã— 7) Surface through Sâ^'Cu Linkage. Journal of Physical Chemistry B, 2005, 109, 13843-13846.	2.6	2

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37	Strain-Mediated Uniform Islands in Stacked Ge/Si(001) Layers. Japanese Journal of Applied Physics, 2004, 43, 7411-7414.	1.5	0
38	Self-assembly of one-dimensional molecular nanostructures on the Ge-covered Si(100) surface. Applied Physics Letters, 2004, 84, 401-403.	3.3	18
39	Film growth of germanium on Ru(0001) studies by scanning tunneling microscopy. Physical Review B, 2004, 70, .	3.2	11
40	EVOLUTION AND ORDERING OF MULTILAYER Ge QUANTUM DOTS ON Si(001). International Journal of Nanoscience, 2004, 03, 579-587.	0.7	1
41	Formation of order molecular nanostructures on the Si(111)-(7Ã—7) surface by patterned assembly. Applied Physics Letters, 2004, 85, 2926-2928.	3.3	4
42	Formation of ordered two-dimensional nanostructures of Cu on the Si()-(7Ã—7) surface. Surface Science, 2003, 531, L378-L382.	1.9	35
43	Fabrication and structural analysis of Al, Ga, and In nanocluster crystals. Physical Review B, 2002, 66, .	3.2	104
44	Scanning tunneling microscopy of endohedral metallofullerene Luâ€“C[sub 82] on C[sub 60] film. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 2388.	1.6	4
45	Ge islanding growth on nitridized Si and the effect of Sb surfactant. Journal of Physics Condensed Matter, 2002, 14, 8939-8946.	1.8	4
46	Shape, orientation and surface structure of Si and Ge nano-particles grown on SiN. Nanotechnology, 2002, 13, 714-719.	2.6	7
47	Investigation of Si and Ge growth on Si3N4/Si. Materials Characterization, 2002, 48, 189-194.	4.4	4
48	An atomic structural model of ()-R30Â° reconstruction proposed for 3Câ€“SiC(111) crystallized islands on Si(111) by C60 precursor. Surface Science, 2001, 476, 1-8.	1.9	9
49	Nitridation of Si(). Surface Science, 2001, 494, 83-94.	1.9	30
50	Scanning Tunneling Microscopy of Endohedral Metallofullerene Tb@C82 on C60 Film and Si(100) 2 Ã— 1 Surface. Journal of Physical Chemistry B, 2001, 105, 11414-11418.	2.6	12
51	Self-assembled growth of cubic silicon carbide nano-islands on silicon. Journal of Crystal Growth, 2001, 224, 83-88.	1.5	6
52	Characterization of Silicon Nitride Thin Films on Si and Overlayer Growth of Si and Ge. Japanese Journal of Applied Physics, 2001, 40, 4292-4298.	1.5	6
53	Surface structures of silicon nitride thin films on Si(111). Thin Solid Films, 2000, 366, 121-128.	1.8	20
54	CrystallineSi3N4thin films on Si(111) and the4Ã—4reconstruction onSi3N4(0001). Physical Review B, 1999, 60, R2146-R2149.	3.2	51

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55	Characterization of structures fabricated by atomic force microscope lithography. Surface Science, 1999, 438, 58-67.	1.9	2
56	Step structures on Br-chemisorbed vicinal Si(111). Surface Science, 1998, 400, 220-231.	1.9	15
57	Evolution of surface morphology of vicinal Si(111) surfaces after aluminum deposition. Surface Science, 1998, 418, 22-31.	1.9	19
58	Step-edge energetics of the Ge/GaAs(001)-(1 Ã— 2) superstructure. Surface Science, 1998, 398, 1-10.	1.9	1
59	Conformal oxides on Si surfaces. Applied Physics Letters, 1997, 71, 1495-1497.	3.3	37
60	Trends in surface roughening: analysis of ion-sputtered GaAs(110). Surface Science, 1996, 364, L511-L518.	1.9	15
61	Effect of ion sputtering on Ge epitaxy on GaAs(110). Applied Physics Letters, 1996, 68, 1660-1662.	3.3	6
62	Enhanced epitaxial growth on substrates modified by ion sputtering: Ge on GaAs(110). Physical Review B, 1996, 53, 11170-11175.	3.2	1
63	Interactions of Br with Si(111)-7Ã—7: Chemisorption, step retreat, and terrace etching. Physical Review B, 1995, 52, 11412-11423.	3.2	38
64	Ion sputtering of GaAs(110): From individual bombardment events to multilayer removal. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2031.	1.6	27
65	Vacancy kinetics and sputtering of GaAs(110). Physical Review B, 1995, 51, 10929-10936.	3.2	27
66	Interaction of 300â€“5000 eV ions with GaAs(110). Applied Physics Letters, 1994, 65, 2818-2820.	3.3	24
67	Growth mode of Ge on GaAs(100). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1994, 12, 1920-1923.	2.1	23
68	Initial stages of Ge/GaAs(100) interface formation. Physical Review B, 1994, 49, 4775-4779.	3.2	16
69	Structural model of sulfur on GaAs(100). Journal of Applied Physics, 1994, 75, 2715-2717.	2.5	27
70	Surface structure of Si(112). Surface Science, 1994, 314, 71-78.	1.9	24
71	Effect of growth rate on the surface morphology of MBE-grown GaAs(001)-(2 Ã— 4). Surface Science, 1994, 302, L269-L274.	1.9	15
72	Surface morphology of MBE-grown GaAs(001)â˜(2 Ã— 4) and GaAs(001)-faceted surfaces investigated by scanning tunneling microscopy. Surface Science, 1993, 287-288, 514-519.	1.9	11

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73	Adsorption of acetylene on the Si(100)â€(2Ã—1) surface. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2250-2254.	2.1	78
74	Performance of an ultrahighâ€vacuum sample transfer system for investigation of molecularâ€beam epitaxy grown semiconductor surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2860-2862.	2.1	15
75	Scanning tunneling microscopy of flat and vicinal molecular-beam epitaxy grown GaAs(001)-(2Ã—4) surfaces: The effect of growth rate. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1374.	1.6	18
76	Analysis of GaAs(100) surfaces prepared with various wet and in situ sample treatments. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1089-1093.	2.1	7
77	Scanning tunneling microscopy studies of Ge/GaAs(100) interface formation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1477.	1.6	3
78	Step-height mixtures on vicinal Si(111) surfaces. Physical Review Letters, 1992, 68, 3885-3888.	7.8	50
79	Scanning tunneling microscopy of the filled and empty arsenic states on the GaAs(001)-(2 Ã— 4) surface. Surface Science, 1992, 278, L147-L151.	1.9	33
80	Surface height correlation functions of vicinal Si(111) surfaces using scanning tunneling microscopy. Surface Science, 1991, 249, L285-L292.	1.9	20
81	The precipitation of kinks on stepped Si(111) surfaces. Journal of Chemical Physics, 1991, 94, 8384-8389.	3.0	18
82	Quantization of terrace widths on vicinal Si(111). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 1868-1873.	2.1	40
83	Terrace-width distributions on vicinal Si(111). Physical Review Letters, 1990, 65, 2430-2433.	7.8	167